

IRF7910

HEXFET® Power MOSFET

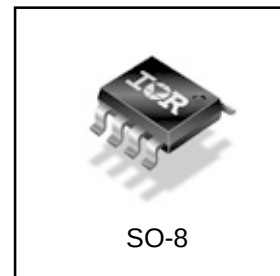
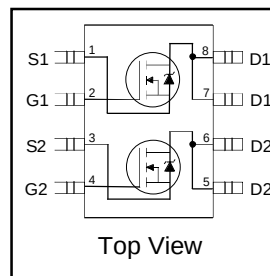
Applications

- High Frequency 3.3V and 5V input Point-of-Load Synchronous Buck Converters for Netcom and Computing Applications
- Power Management for Netcom, Computing and Portable Applications

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	I_D
12V	15m Ω @ $V_{GS} = 4.5V$	10A



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	12	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D @ $T_A = 25^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V	10	A
I_D @ $T_A = 70^\circ C$	Continuous Drain Current, V_{GS} @ 4.5V	7.9	
I_{DM}	Pulsed Drain Current①	79	
P_D @ $T_A = 25^\circ C$	Maximum Power Dissipation④	2.0	W
P_D @ $T_A = 70^\circ C$	Maximum Power Dissipation④	1.3	W
	Linear Derating Factor	16	mW/ $^\circ C$
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient ④	—	62.5	

Notes ① through ④ are on page 8
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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	12	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	11.5	15	m Ω	$V_{GS} = 4.5V, I_D = 8.0A$ ③
		—	20	50		$V_{GS} = 2.8V, I_D = 5.0A$
$V_{GS(th)}$	Gate Threshold Voltage	0.6	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	100	μA	$V_{DS} = 9.6V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 9.6V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -12V$

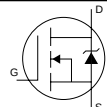
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	18	—	—	S	$V_{DS} = 6.0V, I_D = 8.0A$
Q_g	Total Gate Charge	—	17	26	nC	$I_D = 8.0A$
Q_{gs}	Gate-to-Source Charge	—	4.4	—		$V_{DS} = 6.0V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	5.2	—		$V_{GS} = 4.5V$
Q_{oss}	Output Gate Charge	—	16	—		$V_{GS} = 0V, V_{DS} = 10V$
$t_{d(on)}$	Turn-On Delay Time	—	9.4	—	ns	$V_{DD} = 6.0V$
t_r	Rise Time	—	22	—		$I_D = 8.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	6.3	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	1730	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1340	—		$V_{DS} = 6.0V$
C_{rss}	Reverse Transfer Capacitance	—	330	—		$f = 1.0MHz$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	100	mJ
I_{AR}	Avalanche Current①	—	8.0	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	79		
V_{SD}	Diode Forward Voltage	—	0.85	1.3	V	$T_J = 25^\circ\text{C}, I_S = 8.0A, V_{GS} = 0V$ ③
		—	0.70	—		$T_J = 125^\circ\text{C}, I_S = 8.0A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}, I_F = 8.0A, V_R = 12V$
Q_{rr}	Reverse Recovery Charge	—	60	90	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 125^\circ\text{C}, I_F = 8.0A, V_R = 12V$
Q_{rr}	Reverse Recovery Charge	—	60	90	nC	$di/dt = 100A/\mu s$ ③

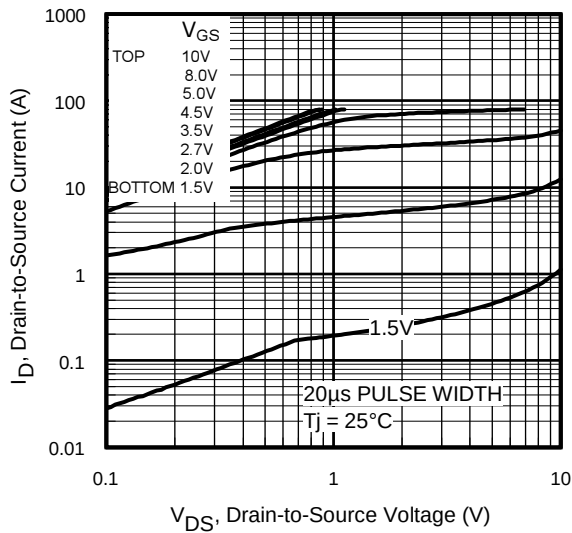


Fig 1. Typical Output Characteristics

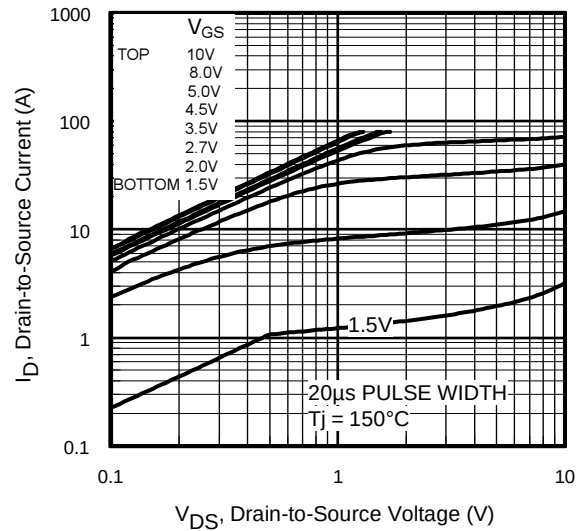


Fig 2. Typical Output Characteristics

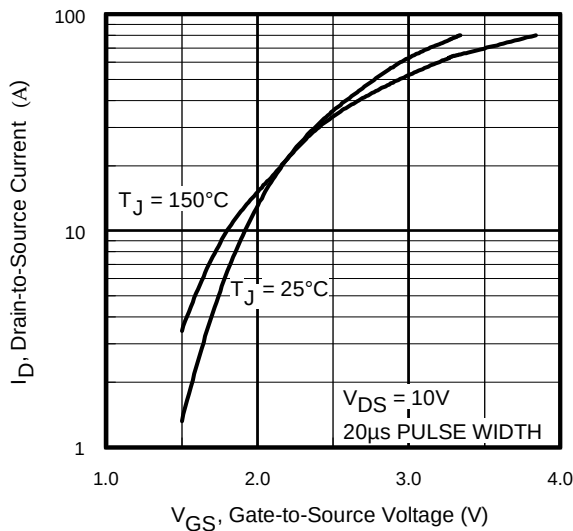


Fig 3. Typical Transfer Characteristics

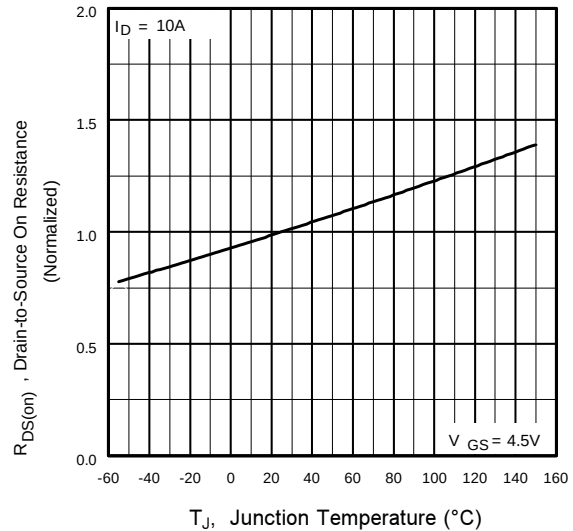


Fig 4. Normalized On-Resistance
Vs. Temperature

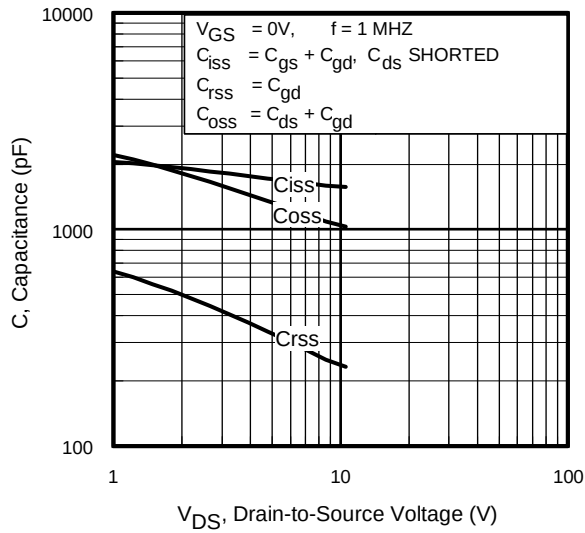


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

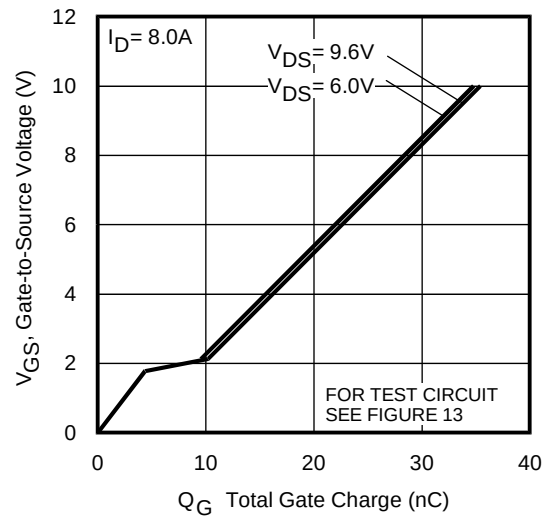


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

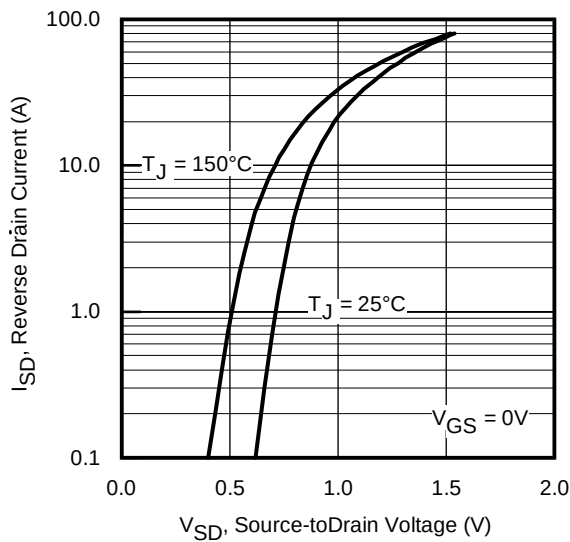


Fig 7. Typical Source-Drain Diode Forward Voltage

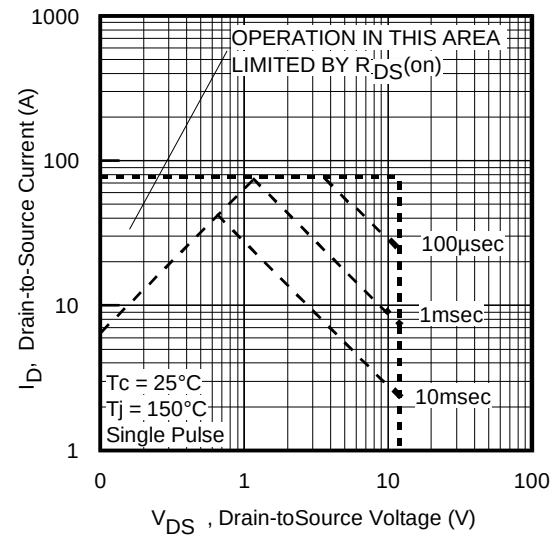


Fig 8. Maximum Safe Operating Area

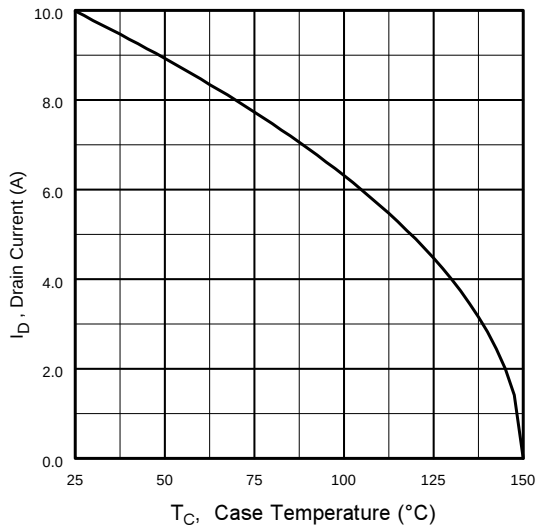


Fig 9. Maximum Drain Current Vs. Ambient Temperature

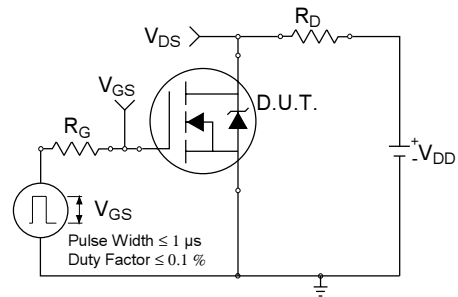


Fig 10a. Switching Time Test Circuit

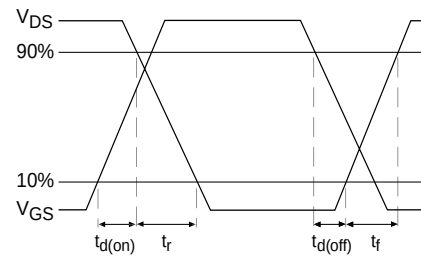


Fig 10b. Switching Time Waveforms

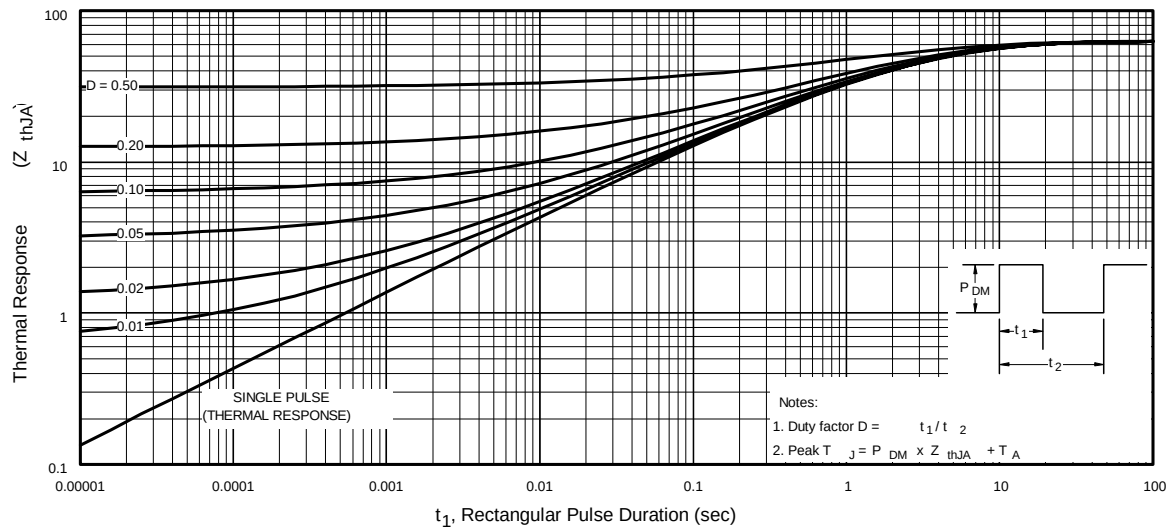


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

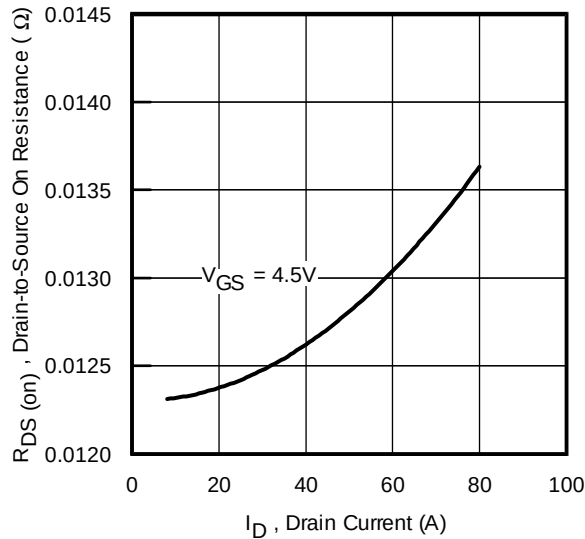


Fig 12. On-Resistance Vs. Drain Current

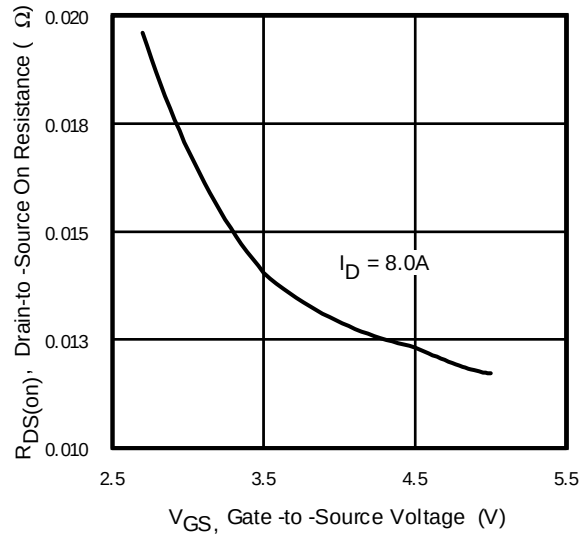


Fig 13. On-Resistance Vs. Gate Voltage

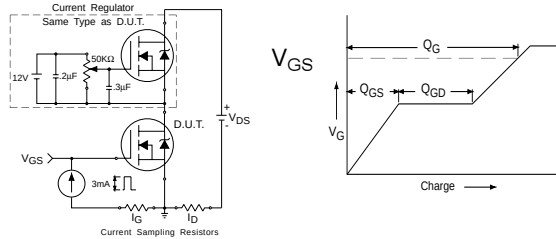


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

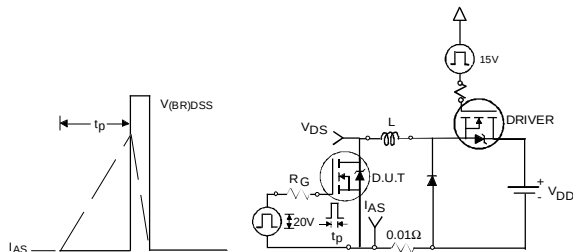


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

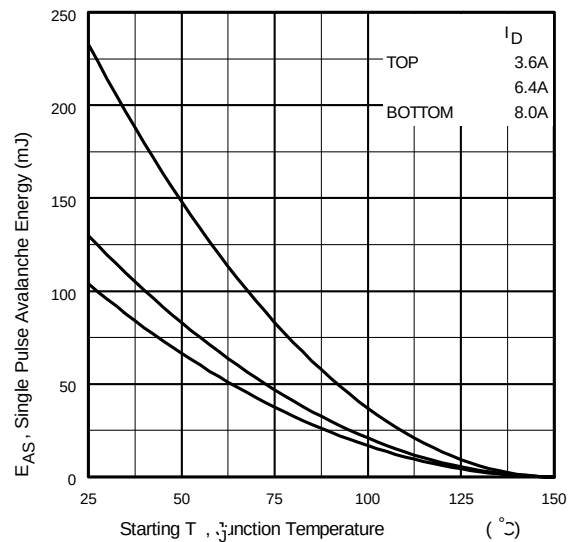
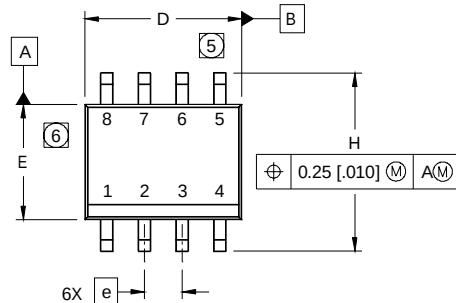
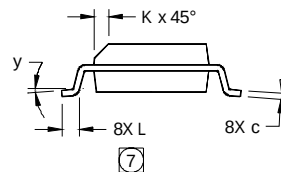
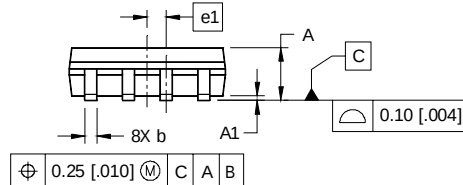


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

SO-8 Package Details

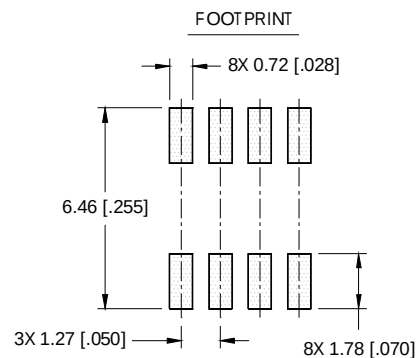


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



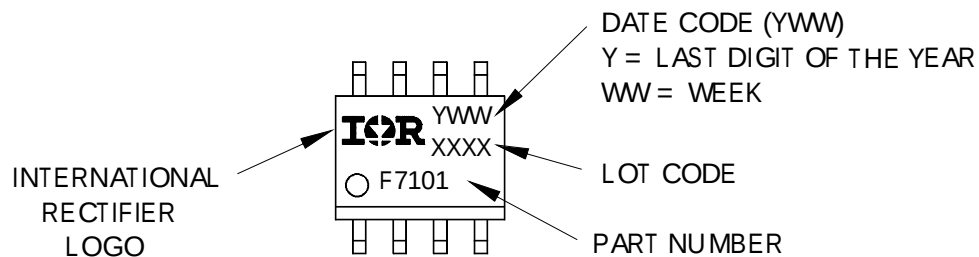
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking

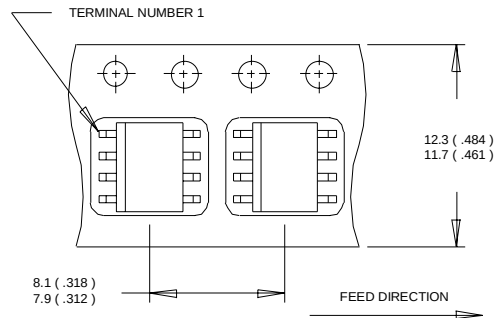
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



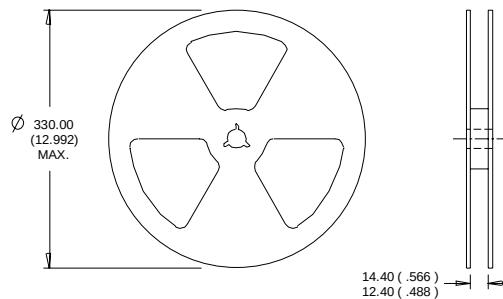
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SO-8 Tape and Reel



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 3.2\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 8.0\text{A}$.
- ③ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board, $t < 10\text{ sec}$

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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IR Rectifier

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